

#### Description

The HXY70N03NF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

#### **General Features**

V<sub>DS</sub> = 30V I<sub>D</sub> =70A

 $R_{DS(ON)} < 8m\Omega V_{GS}=10V$ 

### Application

Battery protection

Load switch

Uninterruptible power supply

### Package Marking and Ordering Information

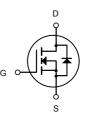
Product ID	Pack	Marking	Qty(PCS)	
HXY70N03NF	DFN5X6-8L	70N03NF XXX YYYY	5000	

### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	30	V		
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20			
l₀@Tc=25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	ous Drain Current, V <sub>GS</sub> @ $10V^1$ 70			
⊳@Tc=100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	51	А		
I₀@T₄=25°C	Continuous Drain Current, VGs @ 10V <sup>1</sup>	15	А		
Id@Ta=70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 1		А		
Ірм	Pulsed Drain Current <sup>2</sup> 160		А		
EAS	Single Pulse Avalanche Energy <sup>3</sup> 115.2		mJ		
las	Avalanche Current	48	А		
P₀@Tc=25°C	Total Power Dissipation <sup>4</sup>	59	W		
P₀@T₄=25°C	Total Power Dissipation <sup>4</sup>	2	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W		
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	2.1	°C/W		







N-Channel MOSFET



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
∆BVbss/∆Tj	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.028		V/°C
		V <sub>GS</sub> =10V , I <sub>D</sub> =30A		6	8	
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		7.5	12	mΩ
VGS(th)	Gate Threshold Voltage		1.2		2.5	V
$\bigtriangleup V_{\text{GS(th)}}$	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA		-6.16		mV/°C
Dss	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
1035	Diam-Source Leakage Current	$V_{DS}$ =24V , $V_{GS}$ =0V , $T_J$ =55°C			5	uA
Igss	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =30A		43		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			20		
Qgs	Gate-Source Charge			7.6		nC
Qgd	Gate-Drain Charge			7.2		
Td(on)	Turn-On Delay Time			7.8		
Tr	Rise Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,		15		
Td(off)	Turn-Off Delay Time			37.3		ns
T <sub>f</sub>	Fall Time	I <sub>D</sub> =15A		10.6		
Ciss	Input Capacitance			2295		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		267		pF
Crss	Reverse Transfer Capacitance			210		•
ls	Continuous Source Current <sup>1,5</sup>				81	А
Іѕм	Pulsed Source Current <sup>2,5</sup>	$-V_G=V_D=0V$ , Force Current			160	Α
Vsd	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1	V
t <sub>rr</sub>	Reverse Recovery Time	, , ,		14		nS
Qrr	Reverse Recovery Charge	_ IF=30A , dI/dt=100A/µs , TJ=25°C		5		nC

### Electrical Characteristics (TJ=25 °C, unless otherwise noted)

Note :

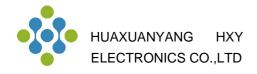
1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%

3. The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =48A

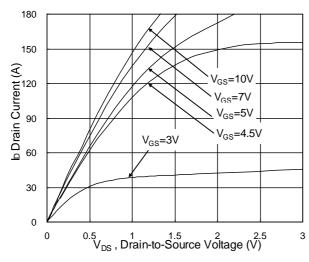
4. The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



# HXY70N03NF N-Channel Enhancement Mode MOSFET

### **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

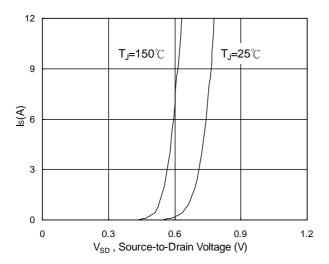


Fig.3 Forward Characteristics of Reverse

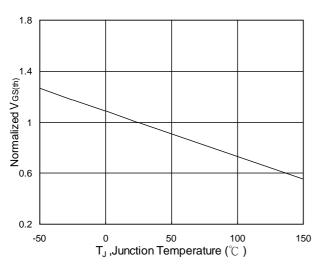


Fig.5 Normalized  $V_{\text{GS(th)}}$  vs.  $T_{\text{J}}$ 

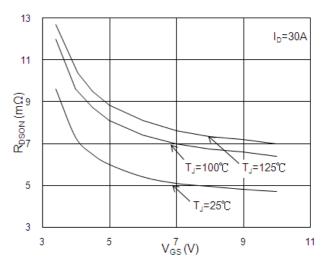


Fig.2 On-Resistance vs. G-S Voltage

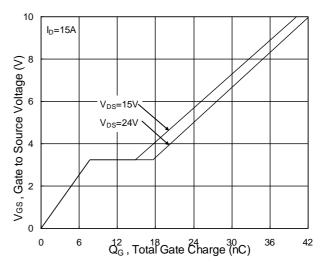


Fig.4 Gate-Charge Characteristics

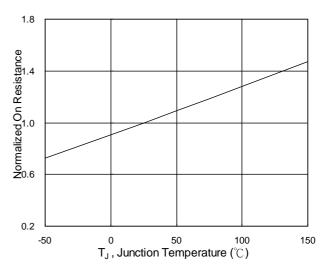
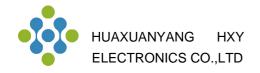


Fig.6 Normalized  $R_{DSON}$  vs.  $T_J$ 



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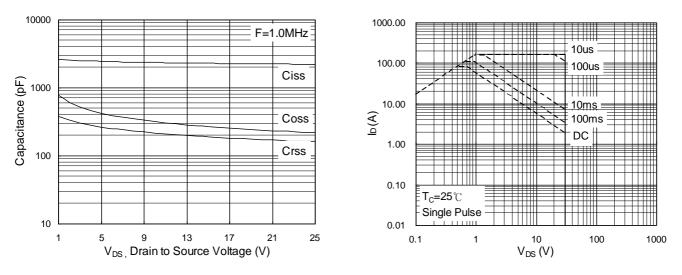


Fig.7 Capacitance

Fig.8 Safe Operating Area

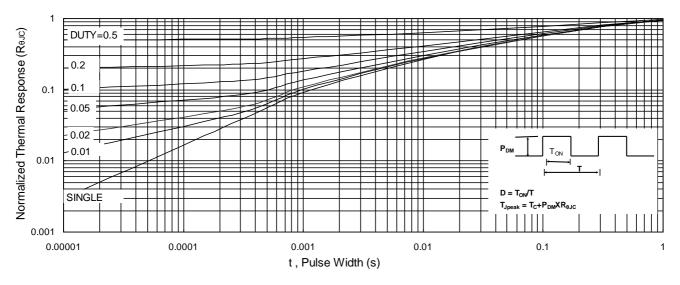


Fig.9 Normalized Maximum Transient Thermal Impedance

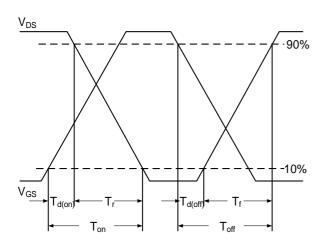


Fig.10 Switching Time Waveform

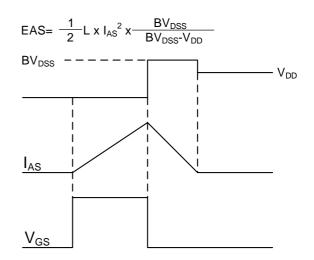
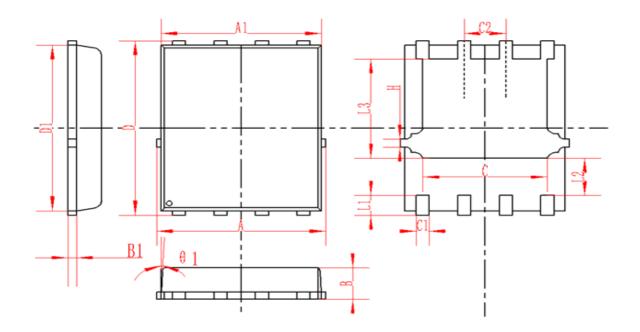


Fig.11 Unclamped Inductive Switching Waveform



## DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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